

# PBSS4021PT

20 V, 3.5 A PNP low  $V_{CEsat}$  (BISS) transistor

Rev. 01 — 29 January 2010

Product data sheet

## 1. Product profile

### 1.1 General description

PNP low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4021NT.

### 1.2 Features

- Very low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain ( $h_{FE}$ ) at high  $I_C$
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

### 1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 1.4 Quick reference data

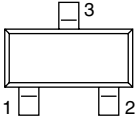
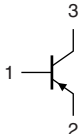
Table 1. Quick reference data

| Symbol      | Parameter                                  | Conditions                       | Min   | Typ | Max  | Unit       |
|-------------|--|----------------------------------|-------|-----|------|------------|
| $V_{CEO}$   | collector-emitter voltage                  | open base                        | -     | -   | -20  | V          |
| $I_C$       | collector current                          |                                  | -     | -   | -3.5 | A          |
| $I_{CM}$    | peak collector current                     | single pulse;<br>$t_p \leq 1$ ms | -     | -   | -8   | A          |
| $R_{CEsat}$ | collector-emitter<br>saturation resistance | $I_C = -4$ A;<br>$I_B = -400$ mA | [1] - | 55  | 82.5 | m $\Omega$ |

[1] Pulse test:  $t_p \leq 300$   $\mu$ s;  $\delta \leq 0.02$ .

## 2. Pinning information

**Table 2. Pinning**

| Pin | Description | Simplified outline  | Graphic symbol  |
|-----|-------------|---|---|
| 1   | base        |  |  |
| 2   | emitter     |   |   |
| 3   | collector   |   |   |

*sym013*

## 3. Ordering information

**Table 3. Ordering information**

| Type number | Package |  |         |
|-------------|---------|--|---------|
|             | Name    | Description                              | Version |
| PBSS4021PT  | -       | plastic surface-mounted package; 3 leads | SOT23   |

## 4. Marking

**Table 4. Marking codes**

| Type number | Marking code <sup>[1]</sup> |
|-------------|-----------------------------|
| PBSS4021PT  | *BJ                         |

- [1] \* = -: made in Hong Kong  
 \* = p: made in Hong Kong  
 \* = t: made in Malaysia  
 \* = W: made in China

## 5. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

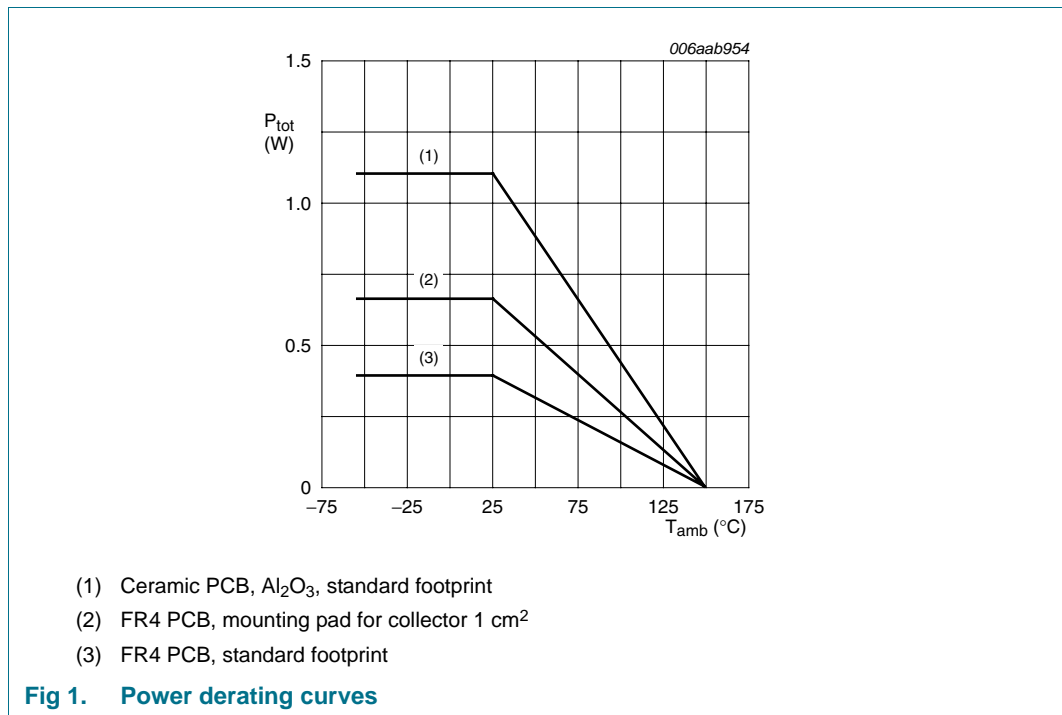
| Symbol    | Parameter                 | Conditions                       | Min | Max  | Unit |
|-----------|---------------------------|----------------------------------|-----|------|------|
| $V_{CBO}$ | collector-base voltage    | open emitter                     | -   | -20  | V    |
| $V_{CEO}$ | collector-emitter voltage | open base                        | -   | -20  | V    |
| $V_{EBO}$ | emitter-base voltage      | open collector                   | -   | -5   | V    |
| $I_C$     | collector current         |                                  | -   | -3.5 | A    |
| $I_{CM}$  | peak collector current    | single pulse;<br>$t_p \leq 1$ ms | -   | -8   | A    |
| $I_B$     | base current              |                                  | -   | -1   | A    |

**Table 5. Limiting values ...continued**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol    | Parameter               | Conditions                  | Min   | Max  | Unit |
|-----------|-------------------------|-----------------------------|-------|------|------|
| $P_{tot}$ | total power dissipation | $T_{amb} \leq 25\text{ °C}$ | [1] - | 390  | mW   |
|           |                         |                             | [2] - | 660  | mW   |
|           |                         |                             | [3] - | 1100 | mW   |
| $T_j$     | junction temperature    |                             | -     | 150  | °C   |
| $T_{amb}$ | ambient temperature     |                             | -55   | +150 | °C   |
| $T_{stg}$ | storage temperature     |                             | -65   | +150 | °C   |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

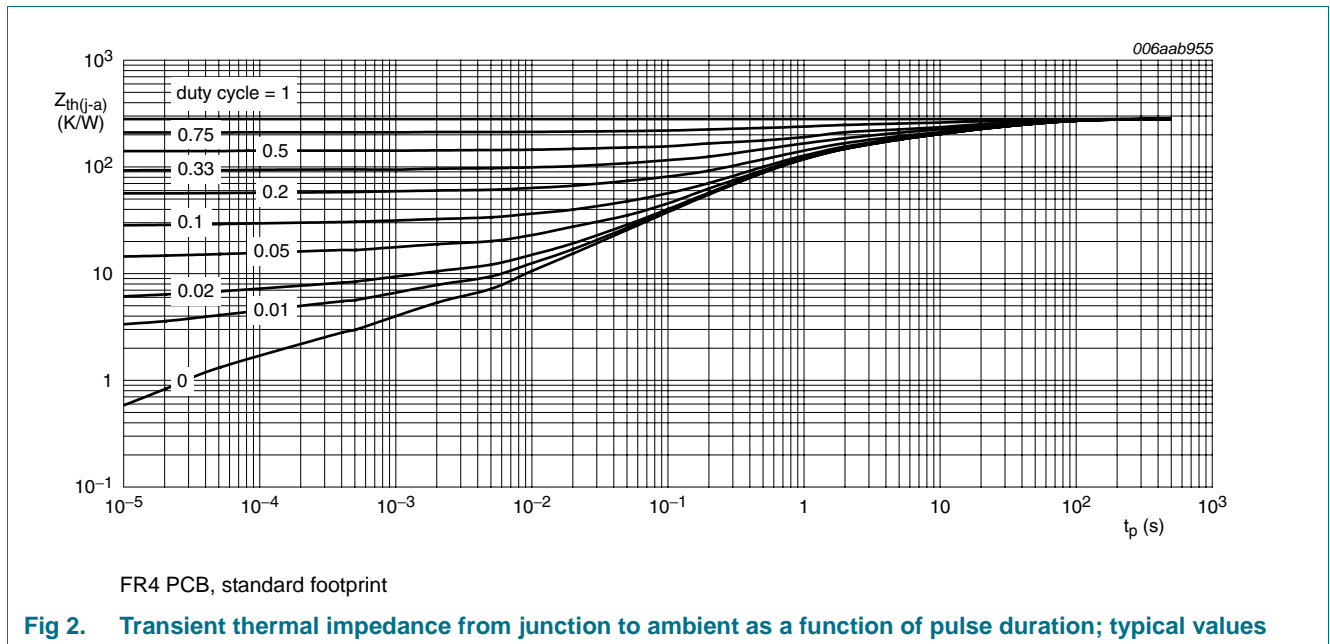


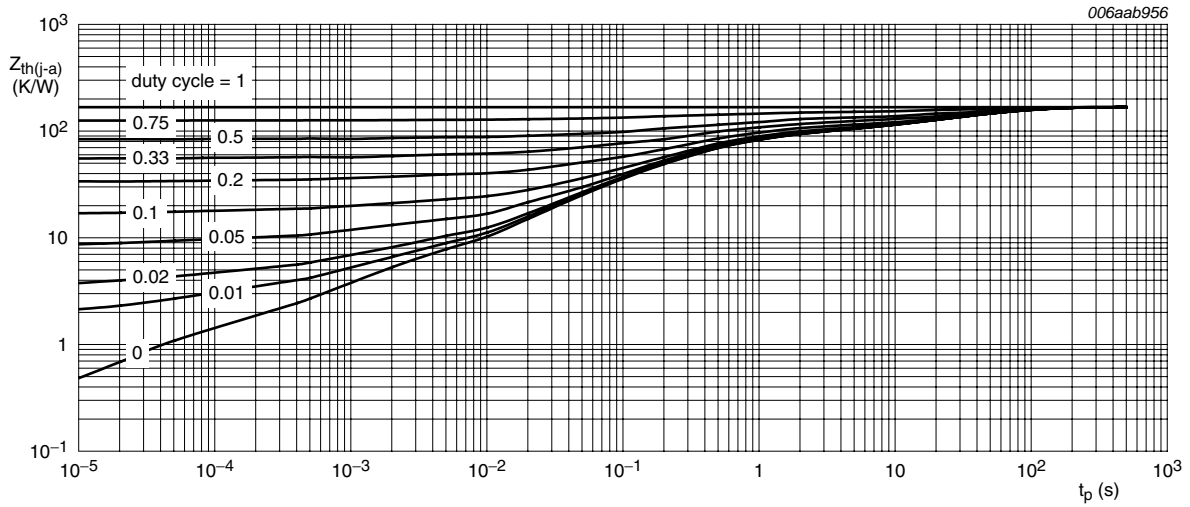
## 6. Thermal characteristics

**Table 6. Thermal characteristics**

| Symbol         | Parameter  | Conditions  | Min | Typ | Max | Unit |     |
|----------------|--|-------------|-----|-----|-----|------|-----|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | [1] | -   | -   | 320  | K/W |
|                |  |             | [2] | -   | -   | 190  | K/W |
|                |  |             | [3] | -   | -   | 115  | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point |             | -   | -   | 62  | K/W  |     |

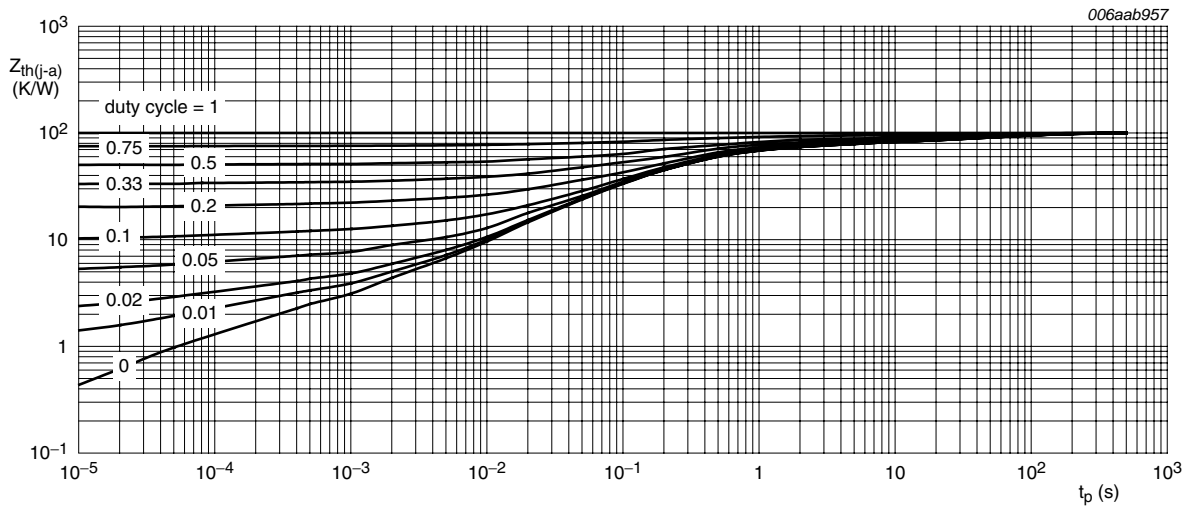
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.





FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>

**Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

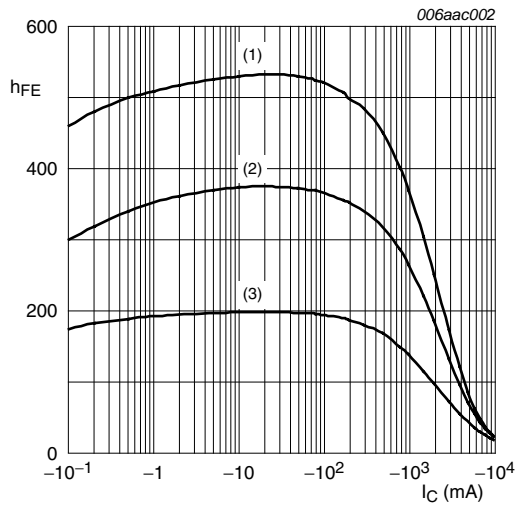
**Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

## 7. Characteristics

**Table 7. Characteristics**
 $T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

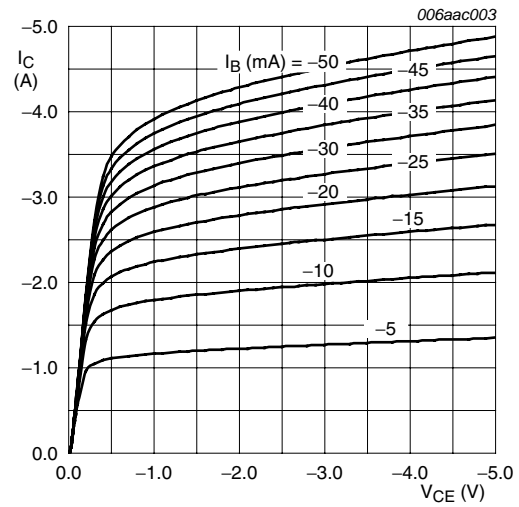
| Symbol      | Parameter                               | Conditions   | Min     | Typ   | Max  | Unit             |
|-------------|---|--|---------|-------|------|------------------|
| $I_{CBO}$   | collector-base cut-off current          | $V_{CB} = -20\text{ V}; I_E = 0\text{ A}$                                    | -       | -     | -100 | nA               |
|             |   | $V_{CB} = -20\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$ | -       | -     | -55  | $\mu\text{A}$    |
| $I_{CES}$   | collector-emitter cut-off current       | $V_{CE} = -16\text{ V}; V_{BE} = 0\text{ V}$                                 | -       | -     | -100 | nA               |
| $I_{EBO}$   | emitter-base cut-off current            | $V_{EB} = -5\text{ V}; I_C = 0\text{ A}$                                     | -       | -     | -100 | nA               |
| $h_{FE}$    | DC current gain                         | $V_{CE} = -2\text{ V}; I_C = -500\text{ mA}$                                 | 250     | 400   | -    |                  |
|             |   | $V_{CE} = -2\text{ V}; I_C = -1\text{ A}$                                    | [1] 200 | 320   | -    |                  |
|             |   | $V_{CE} = -2\text{ V}; I_C = -2\text{ A}$                                    | [1] 140 | 220   | -    |                  |
|             |   | $V_{CE} = -2\text{ V}; I_C = -4\text{ A}$                                    | [1] 60  | 100   | -    |                  |
|             |   | $V_{CE} = -2\text{ V}; I_C = -6\text{ A}$                                    | [1] 30  | 50    | -    |                  |
| $V_{CEsat}$ | collector-emitter saturation voltage    |  | [1]     |       |      |                  |
|             |   | $I_C = -1\text{ A}; I_B = -50\text{ mA}$                                     | -       | -70   | -105 | mV               |
|             |   | $I_C = -1\text{ A}; I_B = -10\text{ mA}$                                     | -       | -115  | -170 | mV               |
|             |   | $I_C = -2\text{ A}; I_B = -40\text{ mA}$                                     | -       | -160  | -240 | mV               |
|             |   | $I_C = -4\text{ A}; I_B = -200\text{ mA}$                                    | -       | -250  | -375 | mV               |
|             |   | $I_C = -4\text{ A}; I_B = -400\text{ mA}$                                    | -       | -220  | -330 | mV               |
| $R_{CEsat}$ | collector-emitter saturation resistance | $I_C = -4\text{ A}; I_B = -400\text{ mA}$                                    | -       | 55    | 82.5 | $\text{m}\Omega$ |
| $V_{BEsat}$ | base-emitter saturation voltage         | $I_C = -1\text{ A}; I_B = -100\text{ mA}$                                    | [1] -   | -0.89 | -1.0 | V                |
|             |   | $I_C = -4\text{ A}; I_B = -400\text{ mA}$                                    | [1] -   | -1.1  | -1.2 | V                |
| $V_{BEon}$  | base-emitter turn-on voltage            | $V_{CE} = -2\text{ V}; I_C = -2\text{ A}$                                    | -       | -0.83 | -0.9 | V                |
| $t_d$       | delay time                              | $V_{CC} = -12.5\text{ V};$   | -       | 10    | -    | ns               |
| $t_r$       | rise time                               | $I_C = -1\text{ A}; I_{Bon} = -0.05\text{ A};$                               | -       | 60    | -    | ns               |
| $t_{on}$    | turn-on time                            | $I_{Boff} = 0.05\text{ A}$   | -       | 70    | -    | ns               |
| $t_s$       | storage time                            |  | -       | 340   | -    | ns               |
| $t_f$       | fall time                               |  | -       | 120   | -    | ns               |
| $t_{off}$   | turn-off time                           |  | -       | 460   | -    | ns               |
| $f_T$       | transition frequency                    | $V_{CE} = -10\text{ V};$<br>$I_C = -100\text{ mA};$<br>$f = 100\text{ MHz}$  | -       | 155   | -    | MHz              |
| $C_c$       | collector capacitance                   | $V_{CB} = -10\text{ V};$<br>$I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$       | -       | 40    | -    | pF               |

[1] Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .



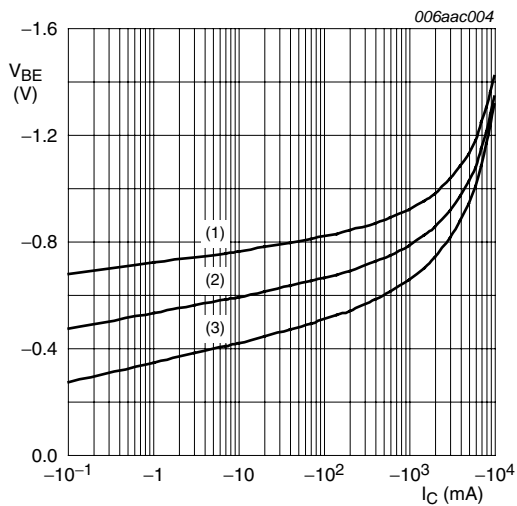
$V_{CE} = -2\text{ V}$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -55\text{ °C}$

**Fig 5. DC current gain as a function of collector current; typical values**



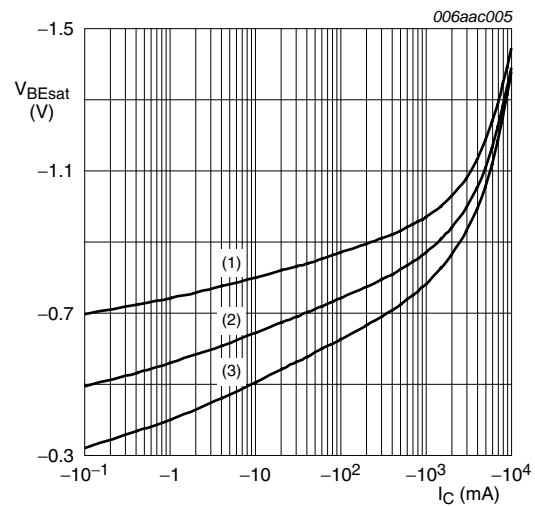
$T_{amb} = 25\text{ °C}$

**Fig 6. Collector current as a function of collector-emitter voltage; typical values**



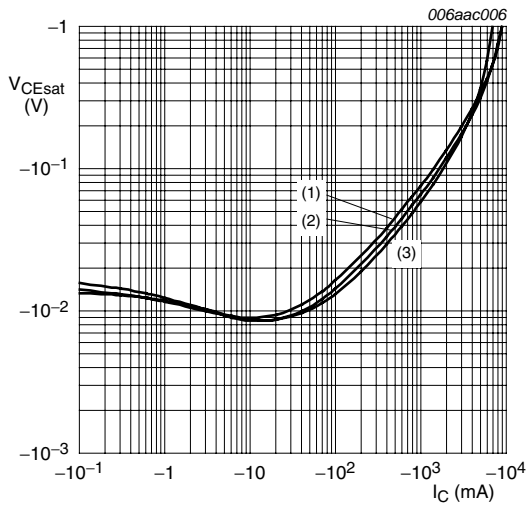
$V_{CE} = -2\text{ V}$   
 (1)  $T_{amb} = -55\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 100\text{ °C}$

**Fig 7. Base-emitter voltage as a function of collector current; typical values**



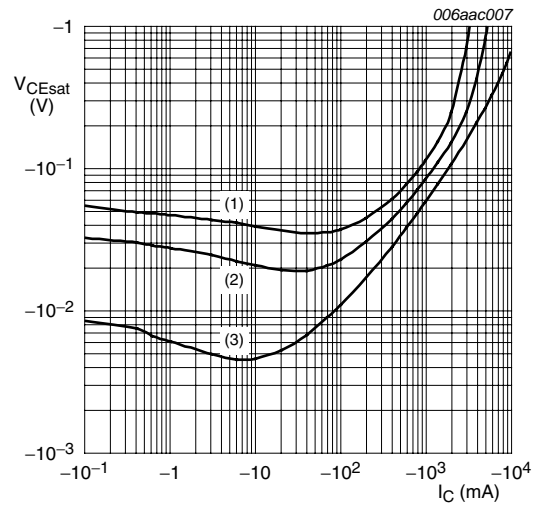
$I_C/I_B = 20$   
 (1)  $T_{amb} = -55\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 100\text{ °C}$

**Fig 8. Base-emitter saturation voltage as a function of collector current; typical values**



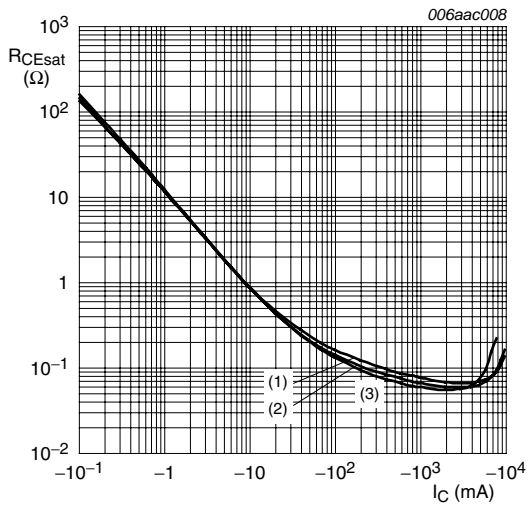
- $I_C/I_B = 20$
- (1)  $T_{amb} = 100\text{ °C}$
  - (2)  $T_{amb} = 25\text{ °C}$
  - (3)  $T_{amb} = -55\text{ °C}$

**Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values**



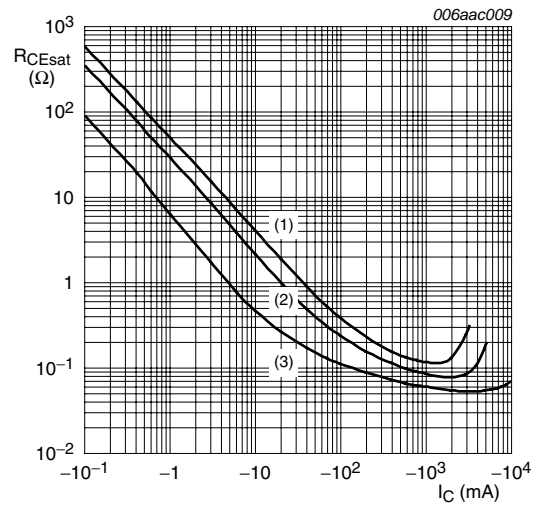
- $T_{amb} = 25\text{ °C}$
- (1)  $I_C/I_B = 100$
  - (2)  $I_C/I_B = 50$
  - (3)  $I_C/I_B = 10$

**Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values**



- $I_C/I_B = 20$
- (1)  $T_{amb} = 100\text{ °C}$
  - (2)  $T_{amb} = 25\text{ °C}$
  - (3)  $T_{amb} = -55\text{ °C}$

**Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values**

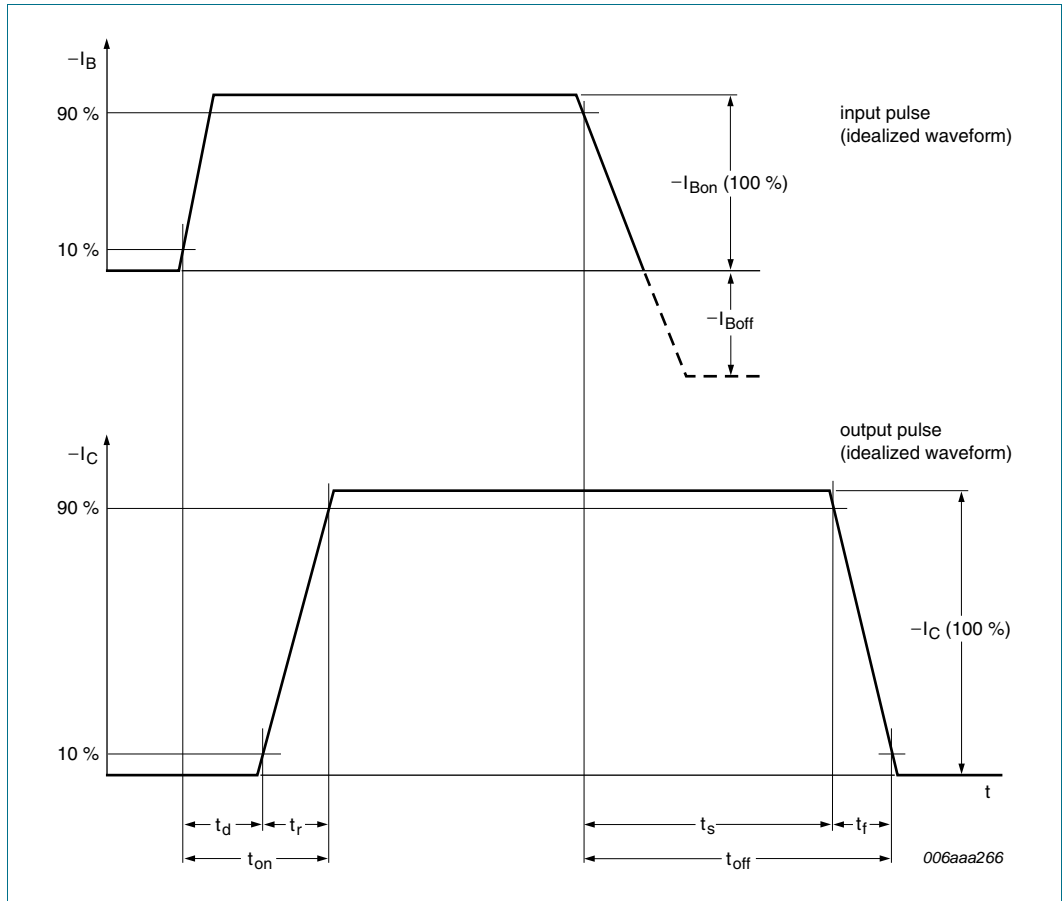


- $T_{amb} = 25\text{ °C}$
- (1)  $I_C/I_B = 100$
  - (2)  $I_C/I_B = 50$
  - (3)  $I_C/I_B = 10$

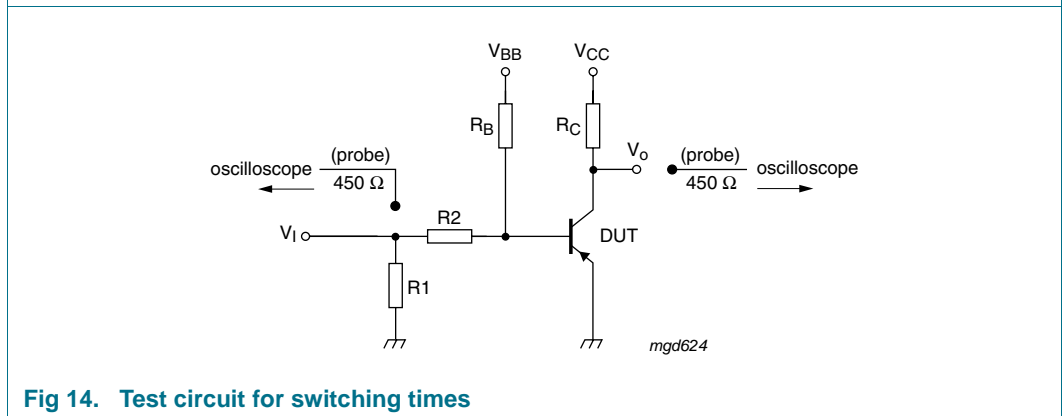
**Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values**



**8. Test information**



**Fig 13. BISS transistor switching time definition**

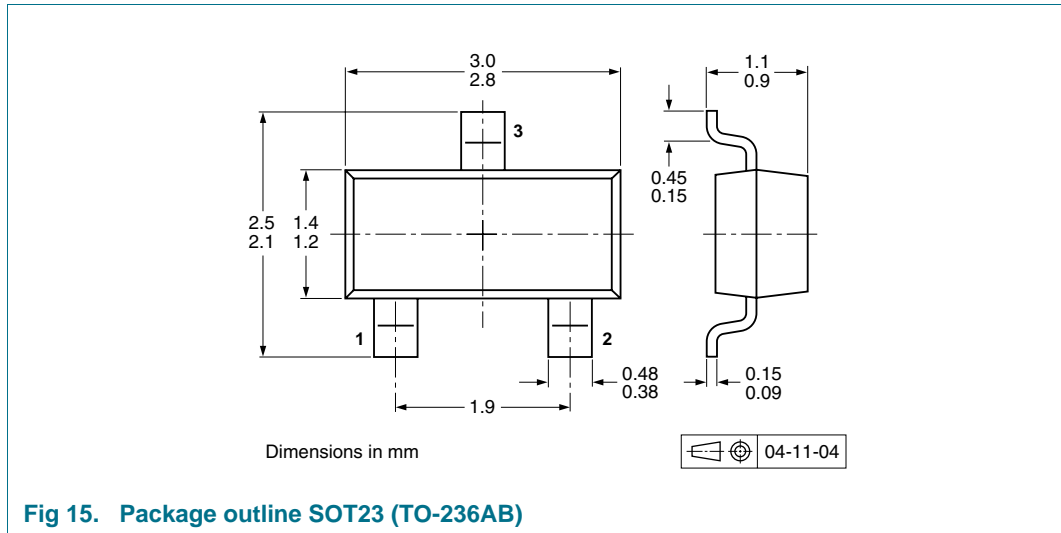


**Fig 14. Test circuit for switching times**

**8.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



## 10. Packing information

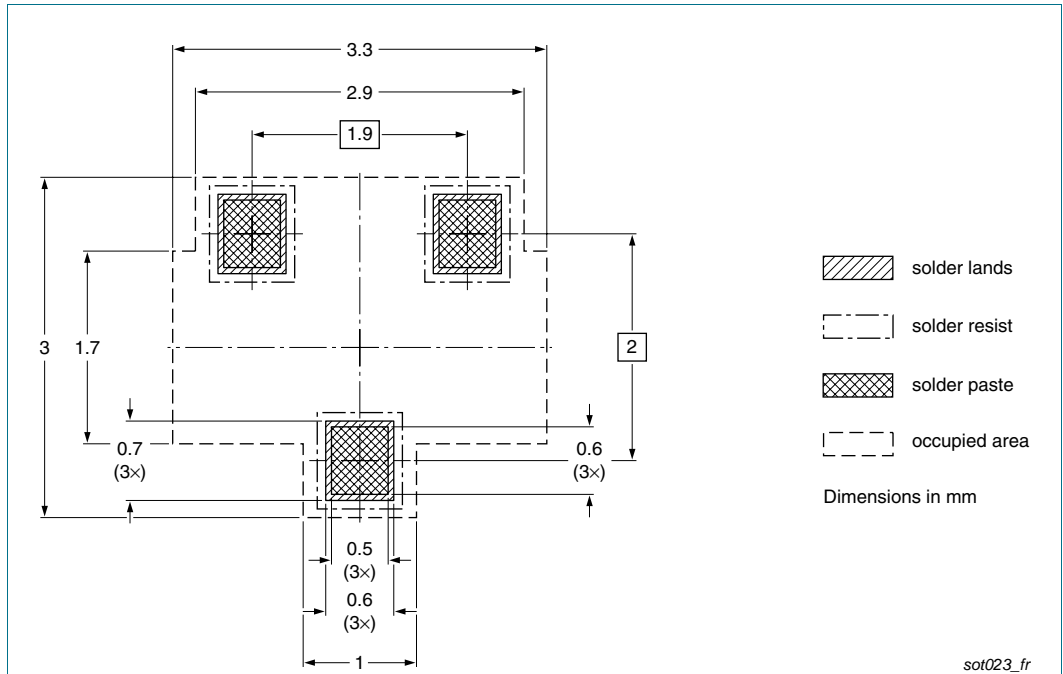
**Table 8. Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

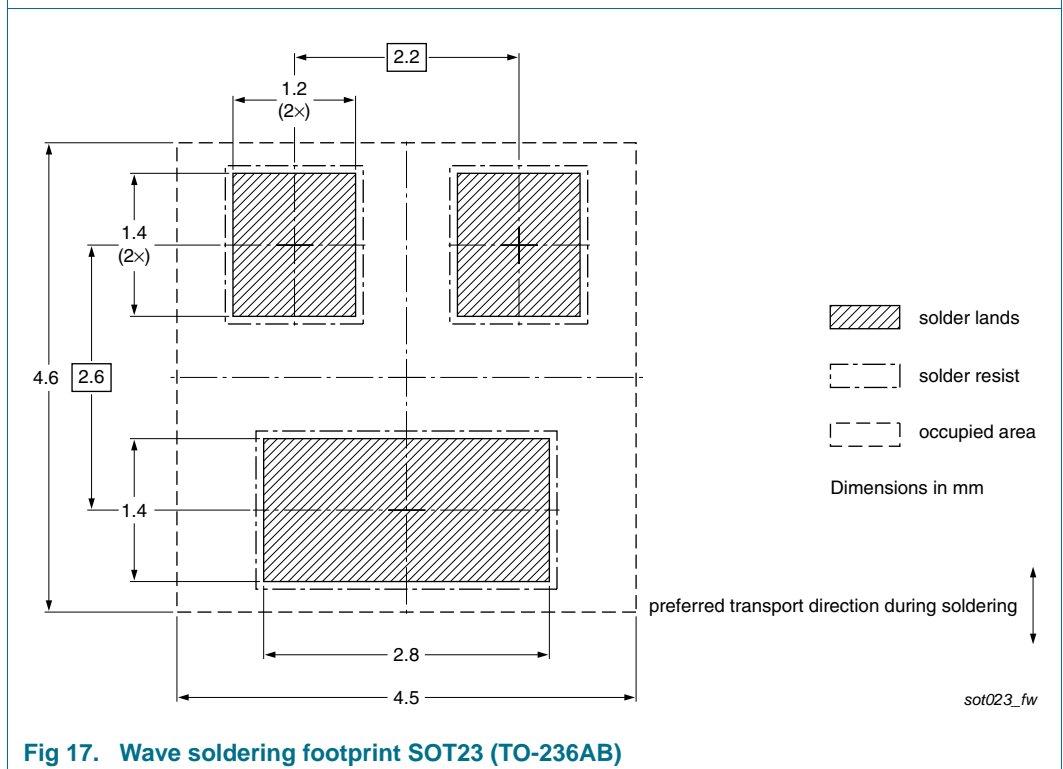
| Type number | Package | Description                    | Packing quantity |       |
|-------------|---------|--------------------------------|------------------|-------|
|             |         |                                | 3000             | 10000 |
| PBSS4021PT  | SOT23   | 4 mm pitch, 8 mm tape and reel | -215             | -235  |

[1] For further information and the availability of packing methods, see [Section 14](#).

**11. Soldering**



**Fig 16. Reflow soldering footprint SOT23 (TO-236AB)**



**Fig 17. Wave soldering footprint SOT23 (TO-236AB)**

## 12. Revision history

Table 9. Revision history

| Document ID  | Release date | Data sheet status  | Change notice | Supersedes |
|--------------|--------------|--------------------|---------------|------------|
| PBSS4021PT_1 | 20100129     | Product data sheet | -             | -          |

## 13. Legal information

### 13.1 Data sheet status

| Document status <sup>[1][2]</sup> | Product status <sup>[3]</sup> | Definition  |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet      | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet    | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet        | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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